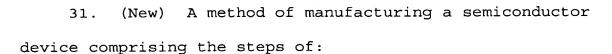


## IN THE CLAIMS

Claims 1-30 are cancelled without prejudice or disclaimer.

1-30. Cancelled.



providing a film substrate having a main surface, a rear surface opposing to the main surface, a plurality of device forming areas of the main surface and electrode members individually separated from one another and formed on the device forming areas;

providing a plurality of semiconductor chips each having a main surface and electrodes formed on the main surface thereof;

arranging the semiconductor chips on respective ones of the device forming areas and electrically connecting the electrodes of the semiconductor chips with electrode members on the respective device forming areas;

forming a resin encapsulator collectively sealing the plurality of device forming areas, the electrode members and the semiconductor chips; and

cutting the resin encapsulator and the film substrate between adjacent device forming areas by dicing;

wherein the electrode members are spaced from a cutting surface resulting from the cutting step.

- 32. (New) A method of manufacturing a semiconductor device according to claim 31, further comprising a step, after the forming step, of separating the resin encapsulator from the film substrate and thereby revealing the electrode members on one side of the resin encapsulator before the cutting step.
- 33. (New) A method of manufacturing a semiconductor device according to claim 32, wherein the cutting step includes a step of sticking dicing tape on another side of the resin encapsulator, wherein the another side is opposed to the one side of the resin encapsulator.
- 34. (New) A method of manufacturing a semiconductor device according to claim 32, wherein further comprising a step of plating the revealed electrode members, after the step of separating the resin encapsulator.

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35. (New) A method of manufacturing a semiconductor device according to claim 34, wherein the plating step is performed before the cutting step.